Silicon PNP Power Transistors 2SB1228

DESCRIPTION

·With TO-220F package
·Complement to type 2SD1830
·High DC current gain.
·Large current capacity and wide ASO.
·Low saturation voltage.
·DARLINGTON

APPLICATIONS

·Suitable for use in control of motor drivers, printer hammer drivers,relay drivers,and constant-voltage regulators.

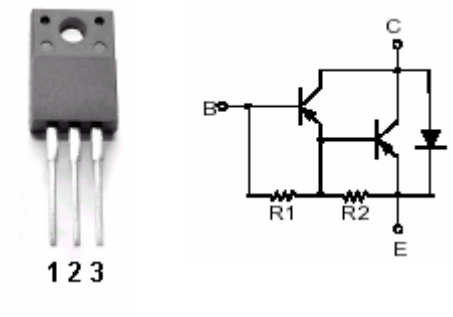

Fig.1 simplified outline (TO-220F) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-110	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-8	A
I_{CM}	Collector current-peak		-12	A
P_C	Collector dissipation	T_C=25□	20	W
			2	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-5mA; I_E=0	-110			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-50mA; R_{BE}=∞	-100			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-4A ; I_B=-8mA		-1.0	-1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-4A ; I_B=-8mA			-2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=-80V;I_E=0			-0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V;I_C=0			-3.0	mA
h_{FE}	DC current gain	I_C=-4A ; V_{CE}=-3V	1500	4000		
f_T	Transition frequency	I_C=-4A ; V_{CE}=-5V		20		MHz

Switching times

t_{on}	Turn-on time	I_C=500I_{B1}=-500I_{B2}=-4A V_{CC}=-50V ,R_L=12.5Ω		0.7		μs
t_{stg}	Storage time			1.4		μs
t_f	Fall time			1.5		μs

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PACKAGE OUTLINE

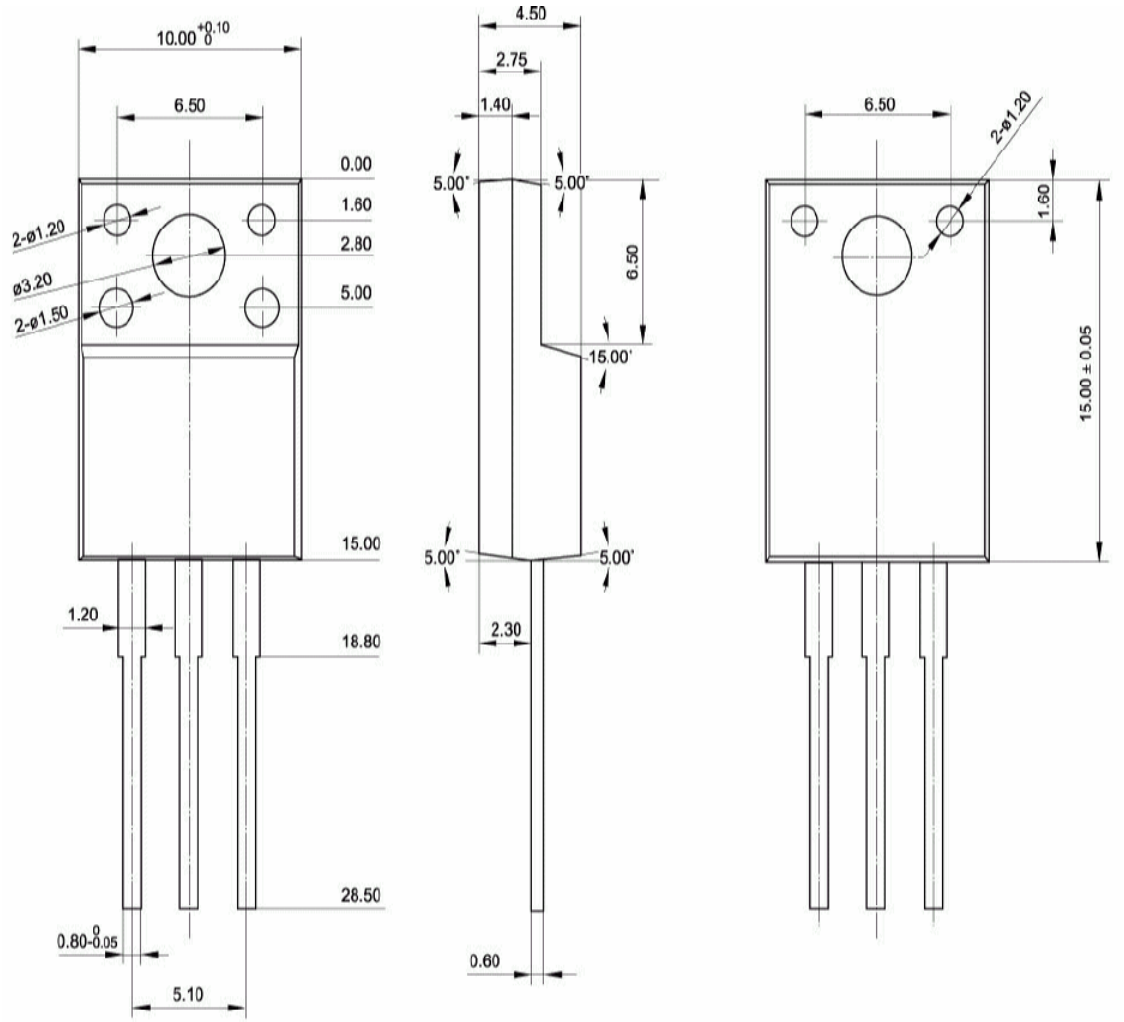

Fig.2 Outline dimensions